

# S-LN74009HCDT3WG

## 40V N-Channel Power MOSFET

### 1. FEATURES

- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

### 2. APPLICATIONS

- Power Tools
- UPS
- Motor Control

### 3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
S-LN74009HCDT3WG	LN74009HC	5000/Tape&Reel

### 4. MAXIMUM RATINGS

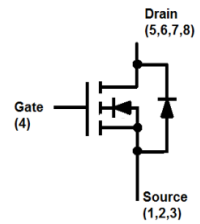
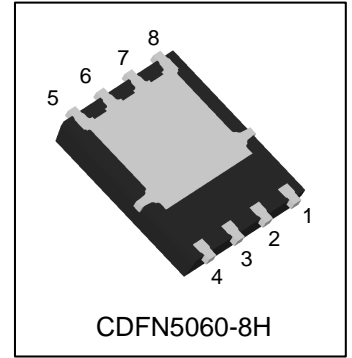
Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDS	40	V
Gate-to-Source Voltage		VGS	± 20	V
Continuous Drain Current(Note 1)	TA =25°C	ID	45	A
	TA =100°C		27	
Pulsed Drain Current(Note 2)		TA =25°C	IDM	180
Continuous Drain Current	TC =25°C	ID	220	A
	TC =100°C		132	
Pulsed Drain Current		TC =25°C	IDM	880
Avalanche Current		IAS	55	A
Avalanche energy(L=0.1mH)		EAS	151	mJ
Power Dissipation(Note 1)	TA =25°C	PD	3.3	W
	TA =100°C		1.7	
Power Dissipation	TC =25°C	PD	150	W
	TC =100°C		75	
Operating Junction and Storage Temperature Range		TJ , TSTG	-55~+175	°C

### 5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Ambient(Note 1)	RθJA	45	°C/W
Junction-to-Case	RθJC	1	

Note:1.Surface mounted on "1.5in x 1.5in" FR4 board using 1\*1 in pad, 2 oz Cu.

2.Pulse width limited by maximum junction temperature.

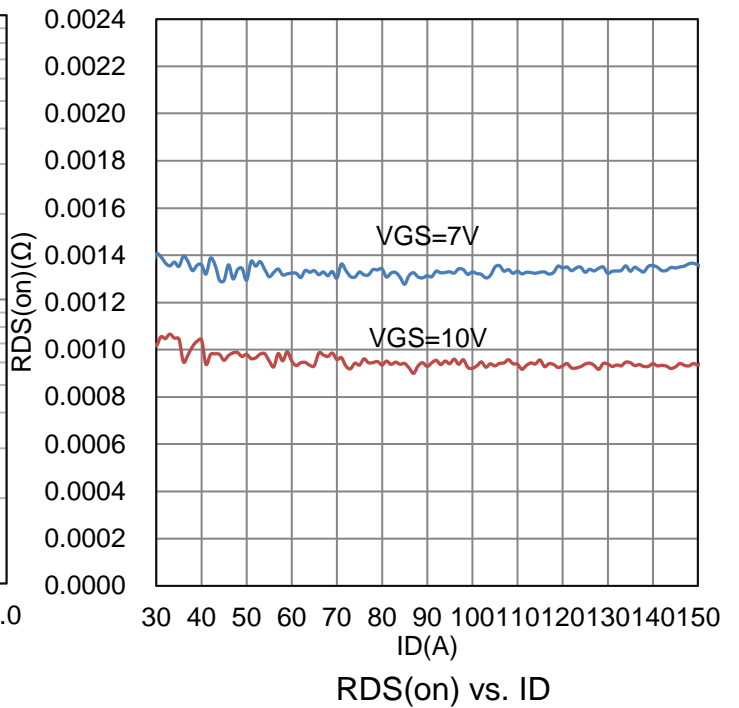
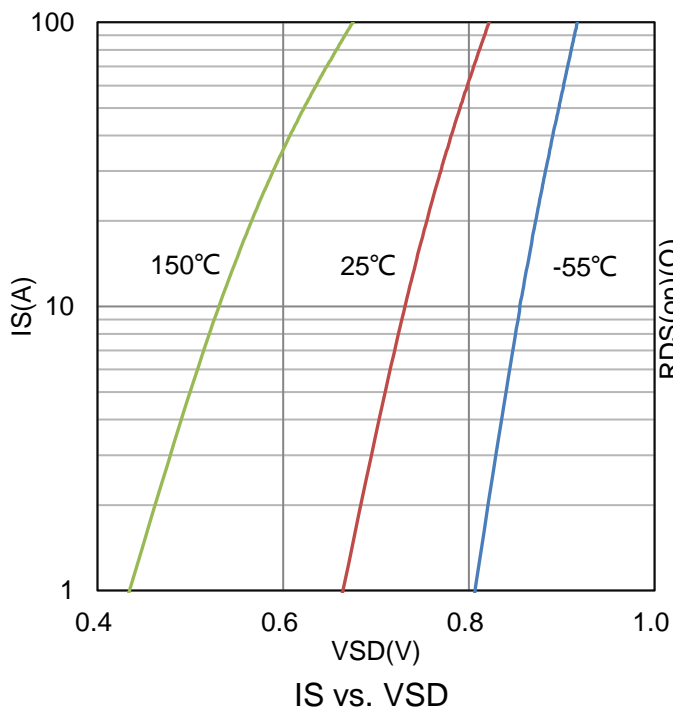
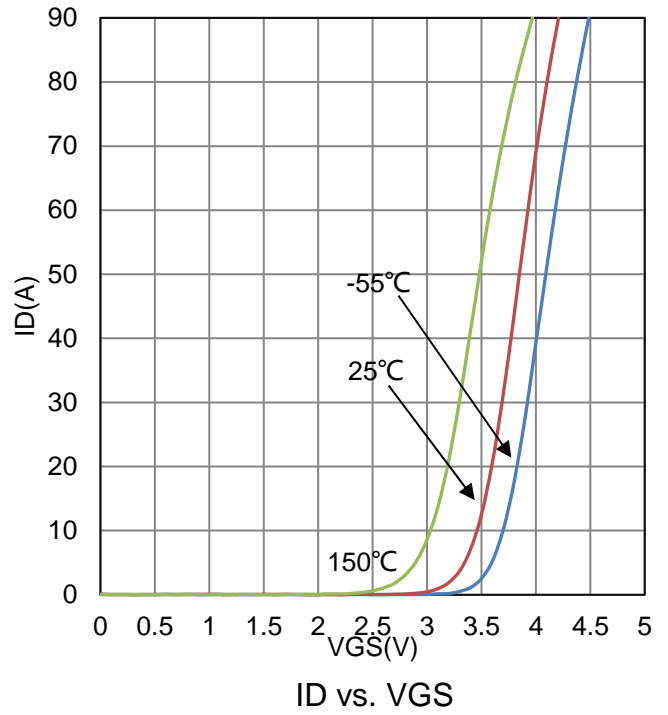
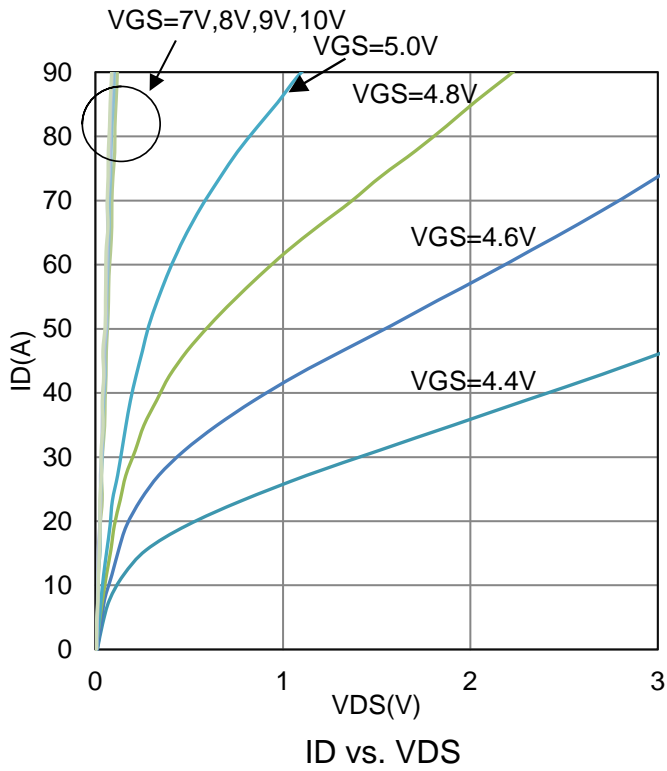


**6. ELECTRICAL CHARACTERISTICS**

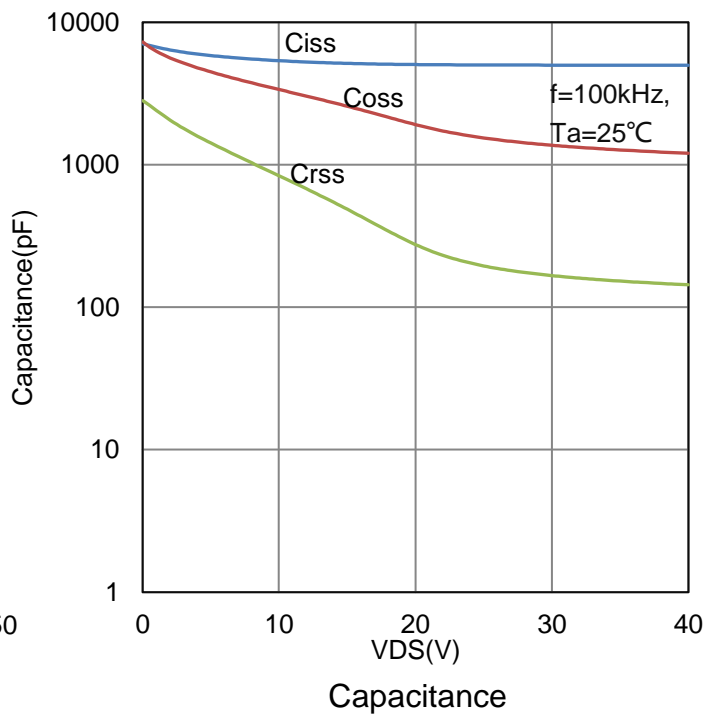
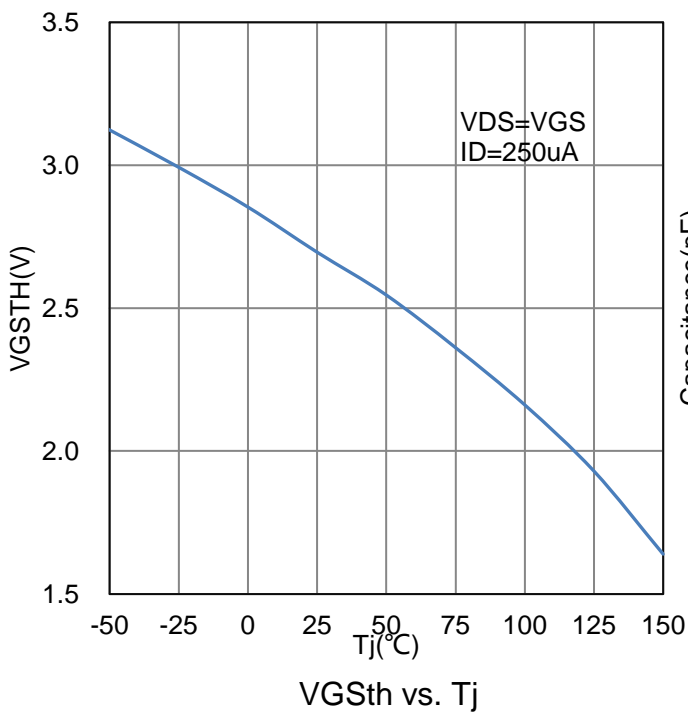
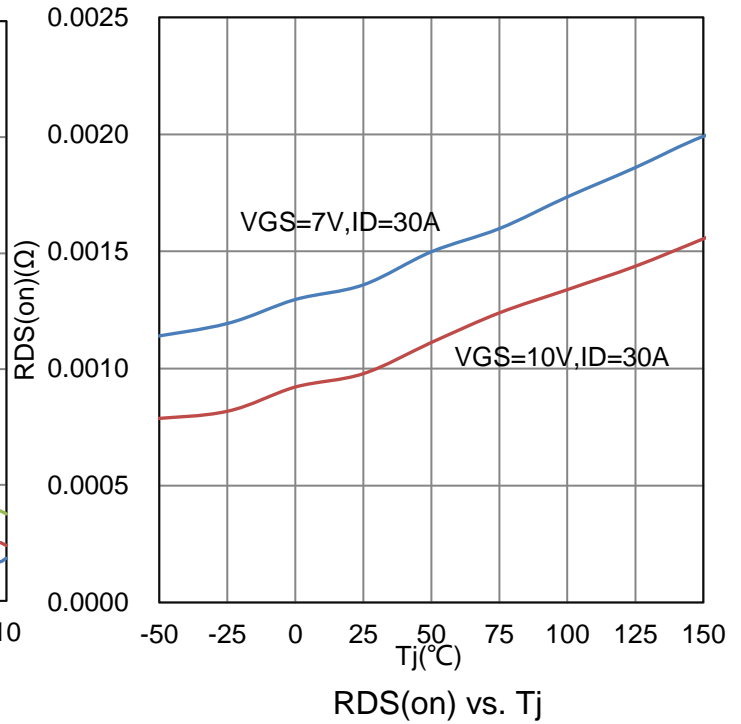
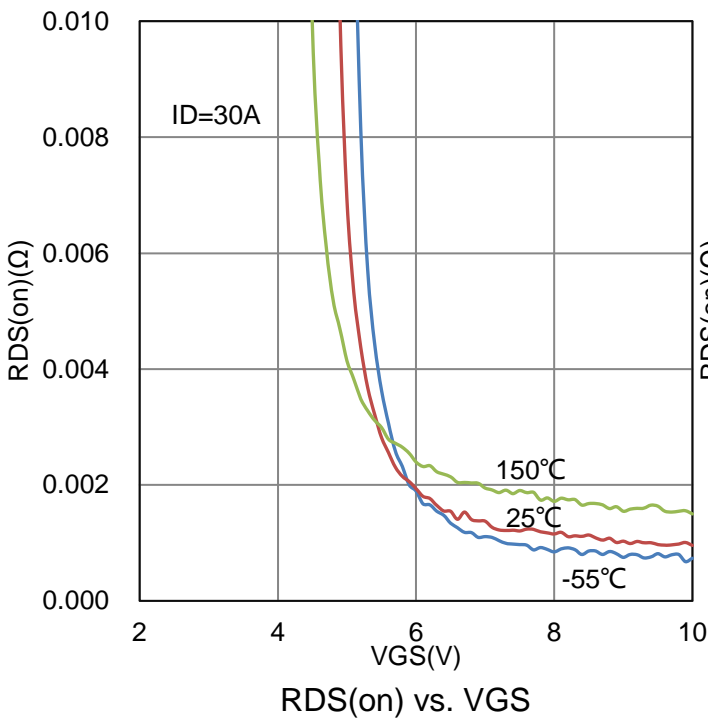
Characteristic	Symbol	Min.	Typ.	Max.	Unit
<b>Static</b>					
Drain to Source Breakdown Voltage (VGS = 0 V, ID = 250 $\mu$ A)	BVDSS	40	-	-	V
Gate-Source Threshold Voltage (VDS = VGS, ID = 250 $\mu$ A)	VGS(th)	2.2	2.8	3.4	V
Gate-Body Leakage (VDS = 0 V, VGS = $\pm$ 20 V)	IGSS	-	-	$\pm$ 100	nA
Zero Gate Voltage Drain Current (VDS = 40 V, VGS = 0 V)	IDSS	-	-	1	$\mu$ A
Drain-Source On-Resistance(Note 3) (VGS = 10 V, ID = 30 A) (VGS = 7 V, ID = 30 A)	RDS(on)	- -	0.76 -	0.92 1.5	m $\Omega$
<b>Dynamic</b>					
Input Capacitance	(VDS = 20 V, VGS = 0 V, f = 100KHz)	Ciss	-	5070	pF
Output Capacitance		Coss	-	1930	
Reverse Transfer Capacitance		Crss	-	280	
Total Gate Charge	(VDS = 20 V, VGS = 10 V, ID = 30 A)	Qg	-	97	nC
Gate-Source Charge		Qgs	-	24	
Gate-Drain Charge		Qgd	-	33	
Turn-On Delay Time	(VDS = 20 V, ID = 30 A, VGS = 10 V, RG = 6 $\Omega$ )	td(on)	-	37	ns
Rise Time		tr	-	52	
Turn-Off Delay Time		td(off)	-	85	
Fall Time		tf	-	72	
<b>Diode characteristics</b>					
Continuous Current TC =25° C	IS	-	-	220	A
Plused Current TC =25° C	ISM	-	-	880	A
Diode Forward Voltage (IS = 20 A, VGS = 0 V)	VSD	-	0.75	1.3	V
Reverse Recovery Time (VR=20V,IF=20A,dIF/dt=100A/us)	trr	-	107	-	ns
Reverse Recovery Charge (VR=20V,IF=20A,dIF/dt=100A/us)	Qrr	-	183	-	nC
Reverse Recovery Current (VR=20V,IF=20A,dIF/dt=100A/us)	IRRM	-	3.45	-	A

3.Pulse test: PW  $\leq$  300us duty cycle  $\leq$  2%.

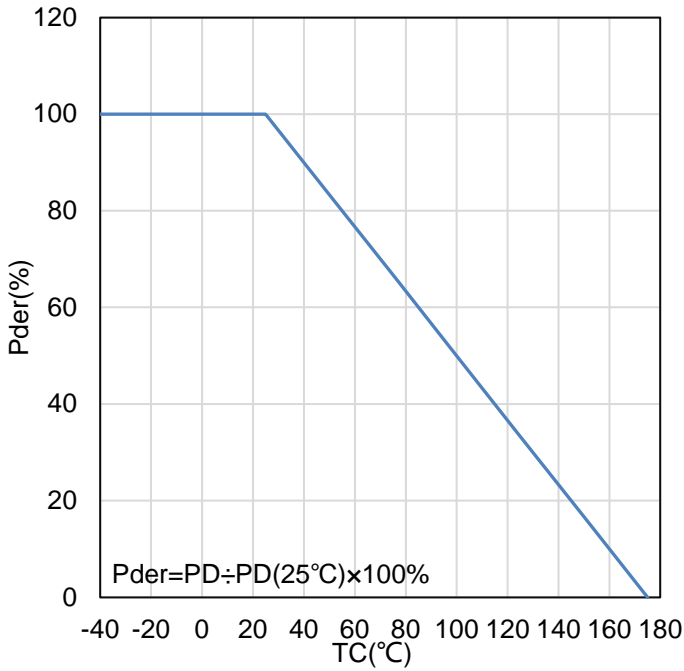
### 7. ELECTRICAL CHARACTERISTICS CURVES



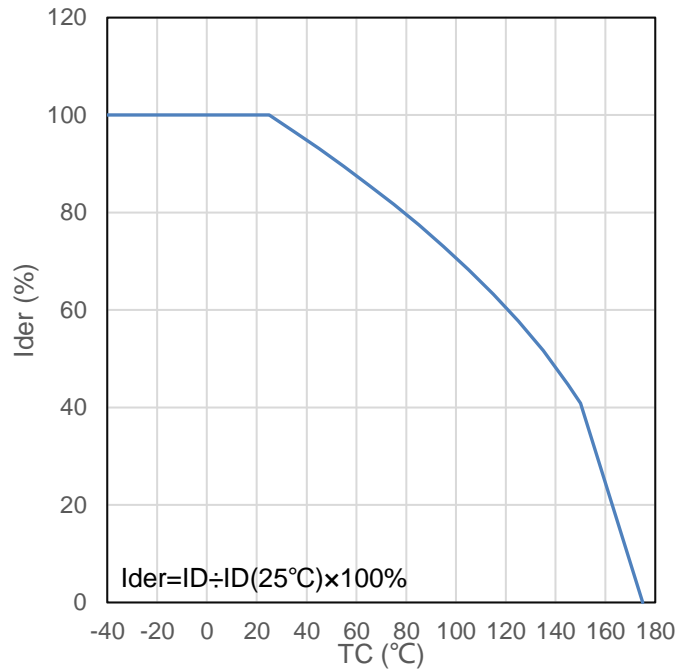
**7. ELECTRICAL CHARACTERISTICS CURVES(Con.)**



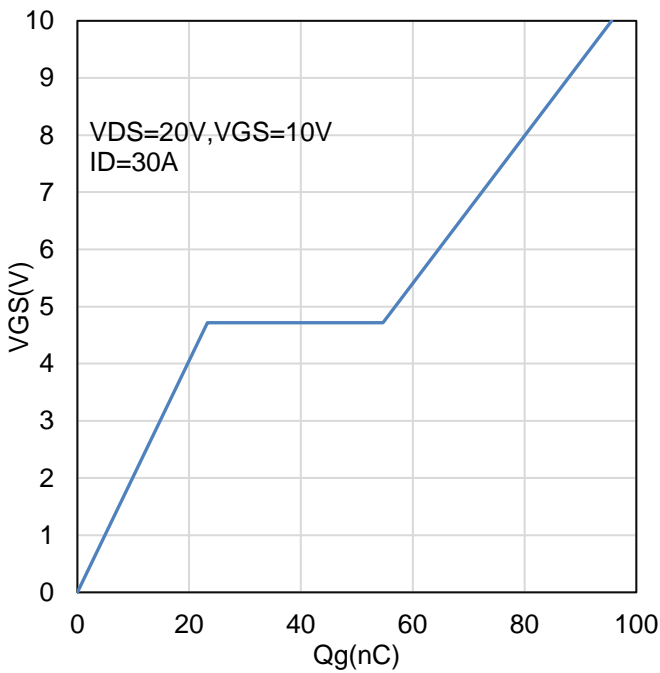
**7. ELECTRICAL CHARACTERISTICS CURVES(Con.)**



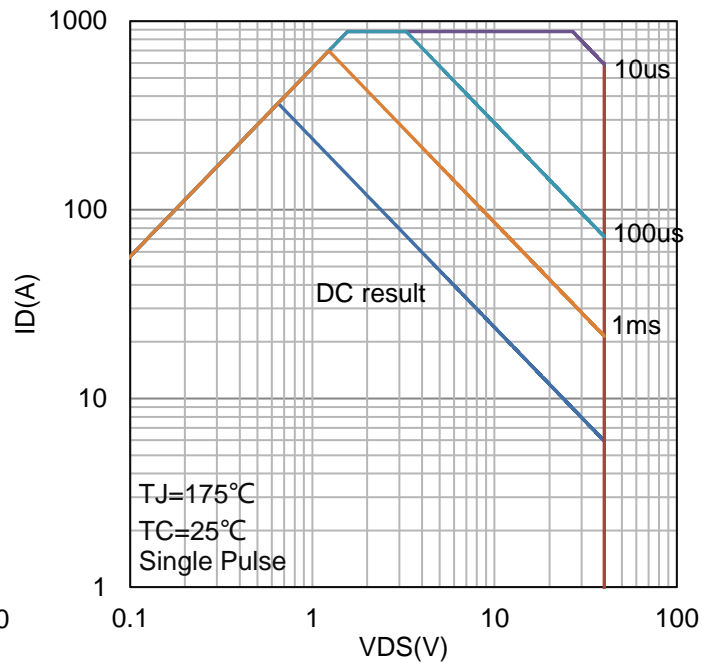
Normalized Derating Curve



Normalized drain Current

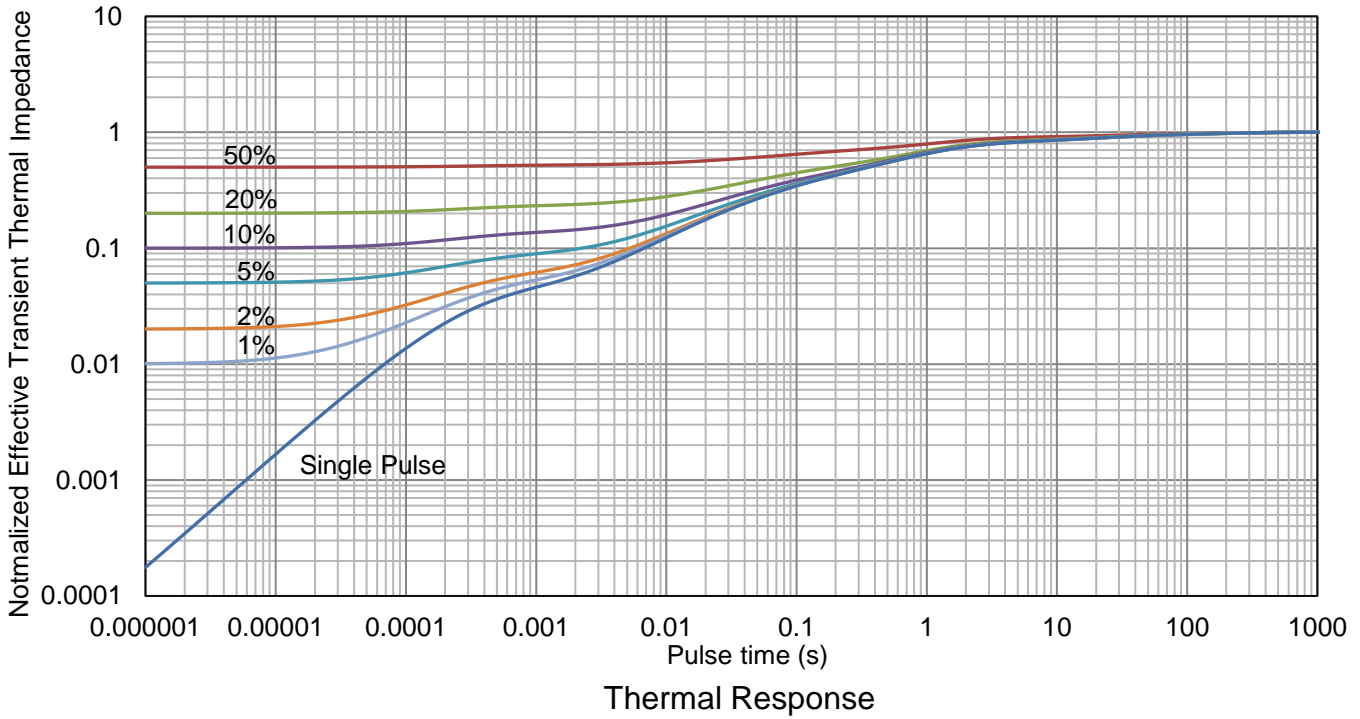


VGS vs. Qg



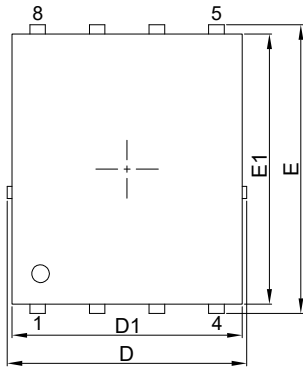
Safe Operating Area

**7. ELECTRICAL CHARACTERISTICS CURVES(Con.)**

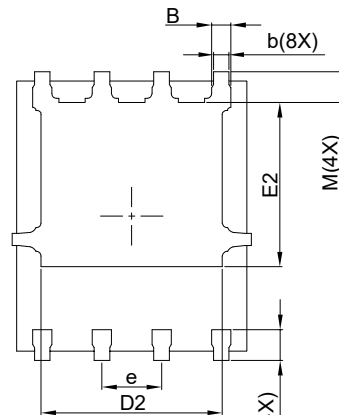


## 8. OUTLINE AND DIMENSIONS

### CDFN5060-8H(T1.00)

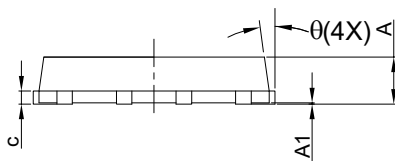


TOP VIEW



BOTTOM VIEW

CDFN5060-8H			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.00	0.02	0.05
E	6.00	6.15	6.30
E1	5.66	5.76	5.86
E2	3.40	3.50	3.60
D	4.95	5.10	5.25
D1	4.80	4.90	5.00
D2	3.76	3.86	3.96
b	0.30	0.35	0.40
B	0.36	0.41	0.46
L	0.56	0.66	0.76
M	0.56	0.66	0.76
e	1.27BSC		
c	0.254REF.		
θ	0°	-	12°

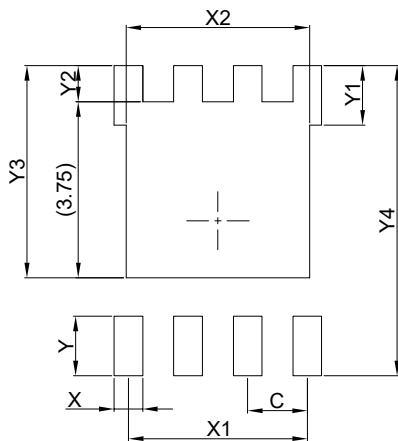


SIDE VIEW

#### GENERAL NOTES

1. Top package surface finish Ra Max0.4um
2. Bottom package surface finish Ra Max0.4um
3. Side package surface finish Ra Max0.4um
4. Protrusion or Gate Burrs shall not exceed 0.05mm per side
5. Offcenter Max0.038mm; Mismatch Max 0.038mm.

## 9. SOLDERING FOOTPRINT



CDFN5060-8H	
DIM	(mm)
C	1.27
X	0.61
X1	3.81
X2	3.91
Y	1.27
Y1	1.27
Y2	0.77
Y3	4.52
Y4	6.61

## **DISCLAIMER**

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
- Before you use our Products for new Porject, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)